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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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1. Renesas Technology Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage.

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2SJ361

Silicon P-Channel MOS FET

RENESAS

ADE-208-143 (Z)
1st. Edition
Aug. 1993

Application

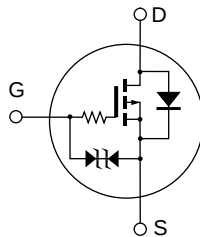
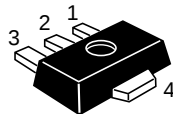
High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- 2.5 V gate drive device can be driven from 3 V source

Outline

UPAK



1. Gate
2. Drain
3. Source
4. Drain

Absolute Maximum Ratings (Ta = 25°C)

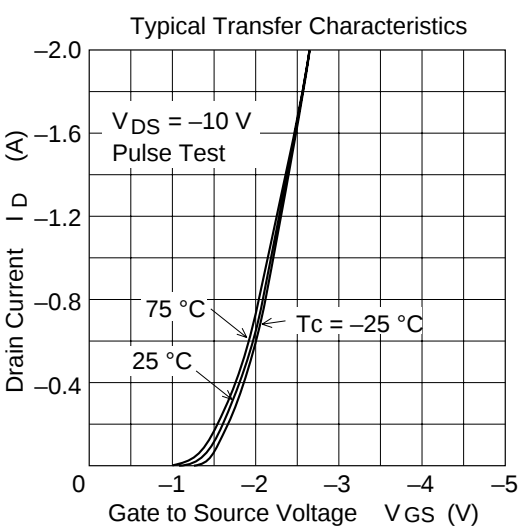
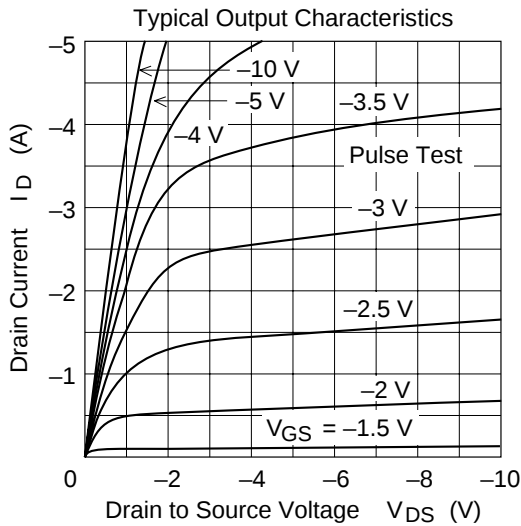
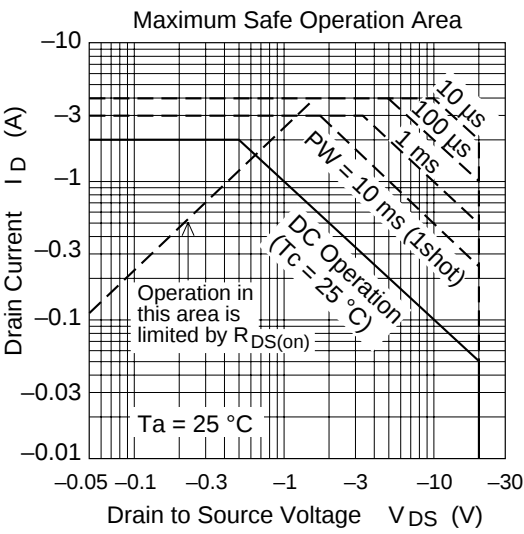
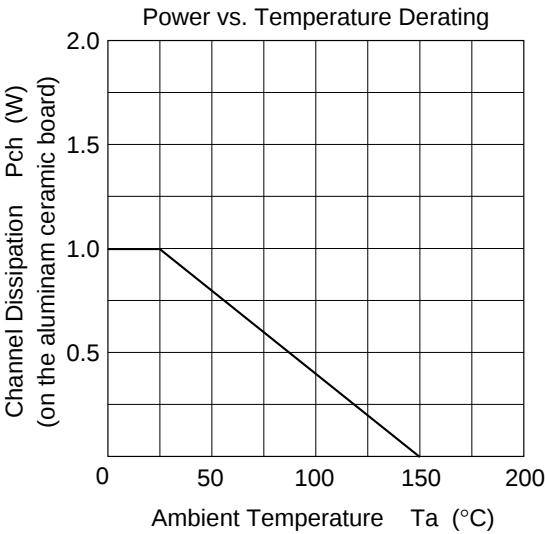
Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	−20	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	−2	A
Drain peak current	I _{D(pulse)} ^{*1}	−4	A
Body to drain diode reverse drain current	I _{DR}	−2	A
Channel dissipation	Pch ^{*2}	1	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	−55 to +150	°C

Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1%
2. Value on the alumina ceramic board (12.5×20×0.7 mm)
3. Marking is “RY”.

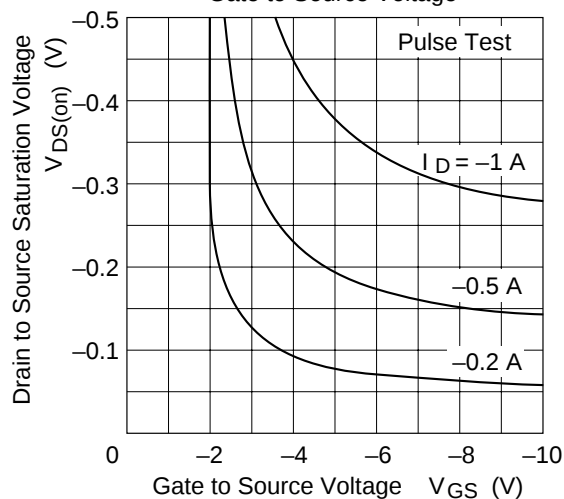
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	-20	—	—	V	$I_D = -10 \text{ mA}$, $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	± 20	—	—	V	$I_G = \pm 100 \text{ }\mu\text{A}$, $V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 16 \text{ V}$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	-10	μA	$V_{DS} = -16 \text{ V}$, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-0.5	—	-1.5	V	$I_D = -1 \text{ mA}$, $V_{DS} = -10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.28	0.4	Ω	$I_D = -1 \text{ A}$, $V_{GS} = -10 \text{ V}$
		—	0.85	1.5	Ω	$I_D = -0.4 \text{ A}$, $V_{GS} = -2.5 \text{ V}$
Forward transfer admittance	$ y_{fs} $	0.15	0.3	—	S	$I_D = -1 \text{ A}$, $V_{DS} = -10 \text{ V}$
Input capacitance	C_{iss}	—	3.2	—	pF	$V_{DS} = -10 \text{ V}$, $V_{GS} = 0$, $f = 1 \text{ MHz}$
Output capacitance	C_{oss}	—	130	—	pF	
Reverse transfer capacitance	C_{rss}	—	0.6	—	pF	
Turn-on delay time	$t_{d(on)}$	—	350	—	ns	$I_D = -1 \text{ A}$, $V_{GS} = -10 \text{ V}$, $R_L = 10 \text{ }\Omega$
Rise time	t_r	—	1650	—	ns	
Turn-off delay time	$t_{d(off)}$	—	7280	—	ns	
Fall time	t_f	—	6950	—	ns	
Body to drain diode forward voltage	V_{DF}	—	-1.0	—	V	$I_F = -2 \text{ A}$, $V_{GS} = 0$
Body to drain diode reverse recovery time	t_{rr}	—	530	—	ns	$I_F = -2 \text{ A}$, $V_{GS} = 0$, $di_F/dt = 20 \text{ A}/\mu\text{s}$

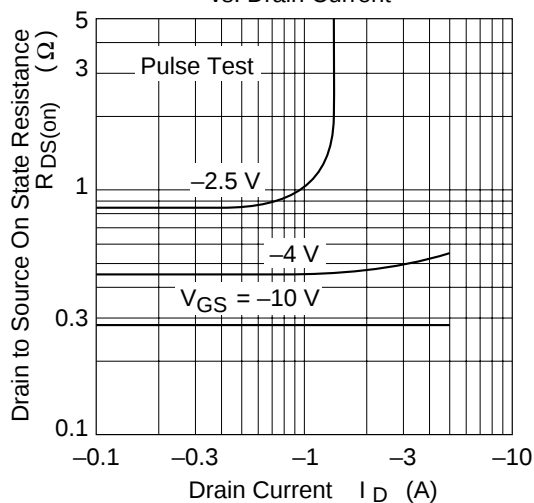
Note: 1. Pulse test



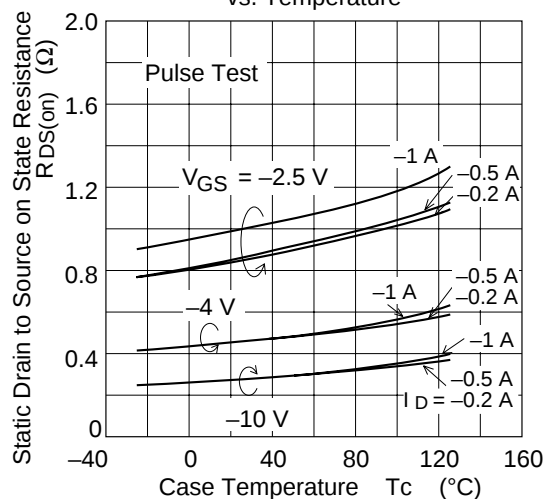
Drain to Source Saturation Voltage vs.
Gate to Source Voltage



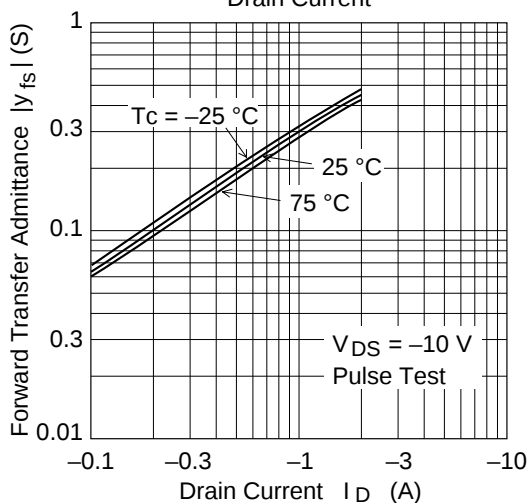
Static Drain to Source on State Resistance
vs. Drain Current



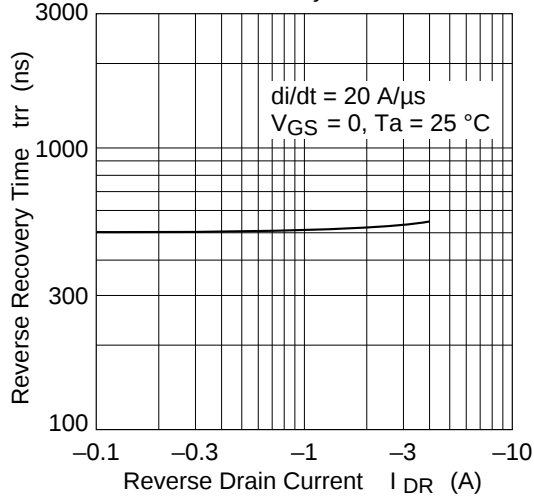
Static Drain to Source on State Resistance
vs. Temperature



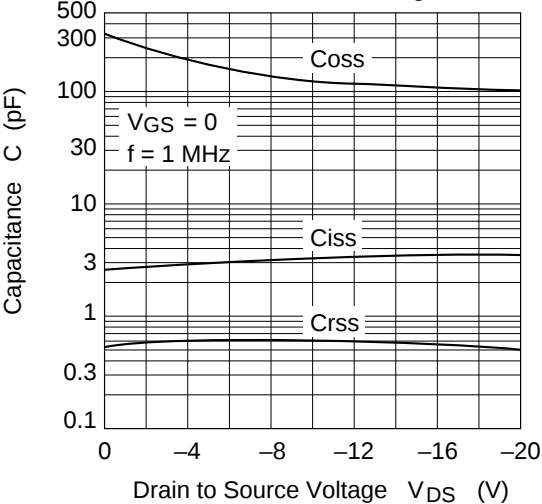
Forward Transfer Admittance vs.
Drain Current



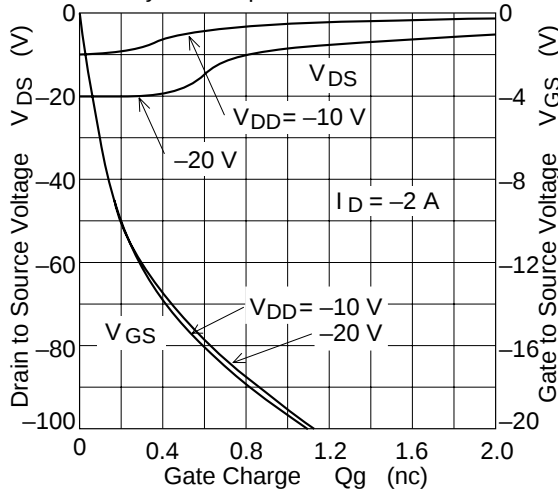
Body–Drain Diode Reverse Recovery Time



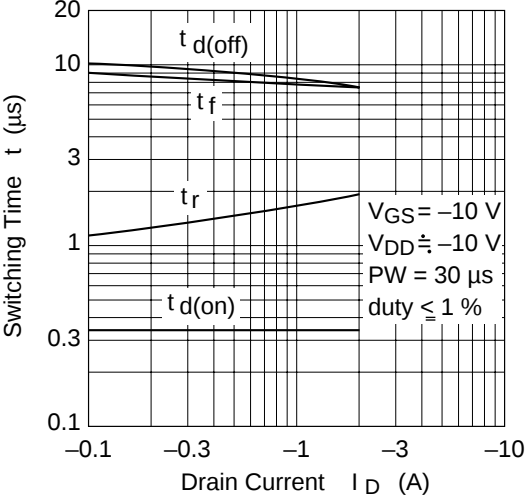
Typical Capacitance vs. Drain to Source Voltage

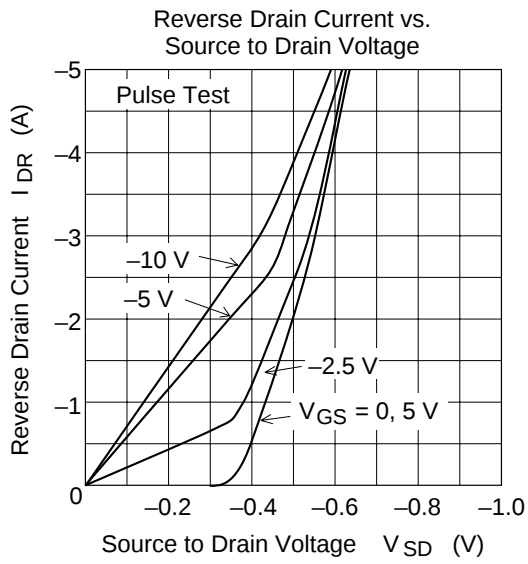


Dynamic Input Characteristics

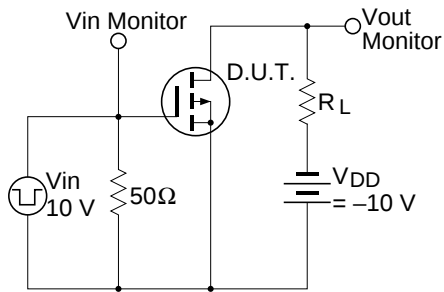


Switching Characteristics

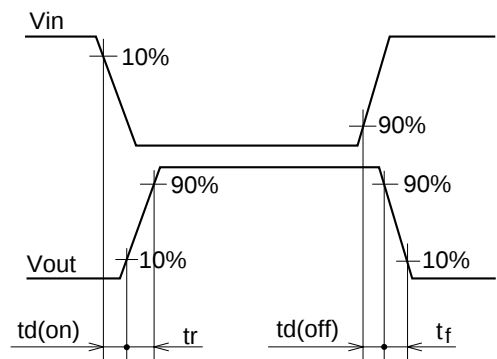




Switching Time Test Circuit

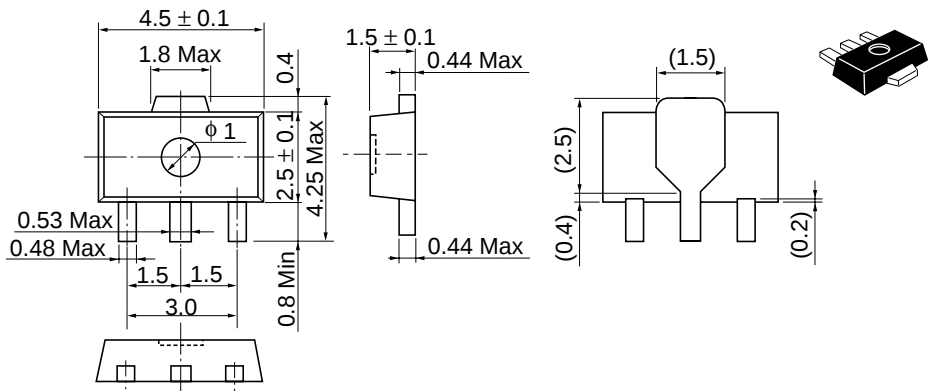


Waveforms



Package Dimensions

As of January, 2001
Unit: mm



Hitachi Code	UPAK
JEDEC	—
EIAJ	Conforms
Mass (reference value)	0.050 g

Cautions

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